ABSTRACT

An alkoxide compound of formula (I) suitable as a material for thin film formation used in thin film formation involving vaporization of a material such as CVD, a material for thin film formation comprising the alkoxide compound, and a process for thin film formation using the material. The process includes vaporizing the material for thin film formation, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.

$$M = \left(-0 - \frac{R_{1}^{1}}{C} - A - N - \frac{R_{3}^{3}}{R_{4}^{2}} \right)_{n}$$
 (1)

wherein one of R¹ and R² represents an alkyl group having 1 to 4 carbon atoms, and the other represents a hydrogen atom or an alkyl group having 1 to 4 carbon atoms; R³ and R⁴ each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.

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